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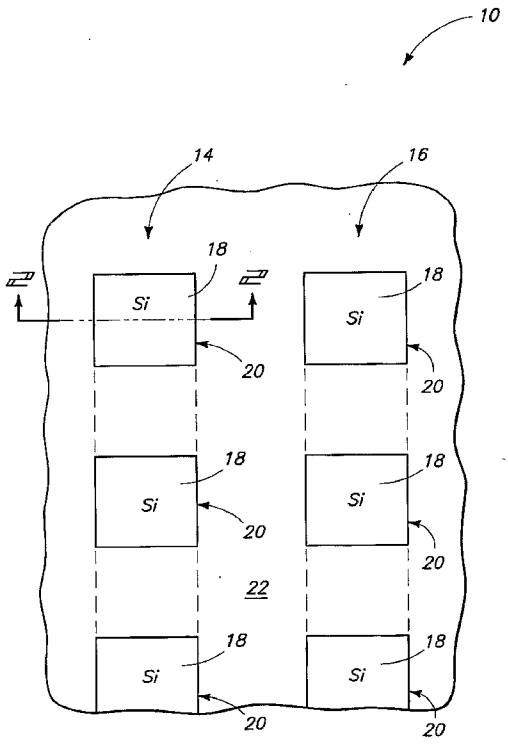
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(54) **Title:** CAPACITORLESS ONE TRANSISTOR DRAM CELL, INTEGRATED CIRCUITRY COMPRISING AN ARRAY OF CAPACITORLESS ONE TRANSISTOR DRAM CELLS, AND METHODS OF FORMING LINES OF CAPACITORLESS ONE TRANSISTOR DRAM CELLS



(57) **Abstract:** This invention includes a capacitorless one transistor DRAM cell that includes a pair of spaced source/drain regions received within semiconductive material. An electrically floating body region is disposed between the source/drain regions within the semiconductive material. A first gate spaced is apart from and capacitively coupled to the body region between the source/drain regions. A pair of opposing conductively interconnected second gates are spaced from and received laterally outward of the first gate. The second gates are spaced from and capacitively coupled to the body region laterally outward of the first gate and between the pair of source/drain regions. Methods of forming lines of capacitorless one transistor DRAM cells are disclosed.

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